

MCC's New 1700V SiC MOSFET: High-Voltage Performance, Low On-Resistance

1700V SiC MOSFET



Features

- High blocking voltage capability (1700V)
- Ultra-low on-resistance (400mΩ) enhances efficiency
- Low capacitance enables faster switching
- Excellent thermal stability
- High operating junction temperature (to +175°C)
- Standard TO-247AB package



Benefits

Our SiC MOSFET's ultra-low on-resistance of only 400mΩ minimizes conduction losses and ramps up energy efficiency in power applications.

High blocking voltage capability of 1700V and low capacitance enable high-speed switching, improving performance in frequency-sensitive applications.

Applications



EV Charging Stations



Base Station Power Supplies

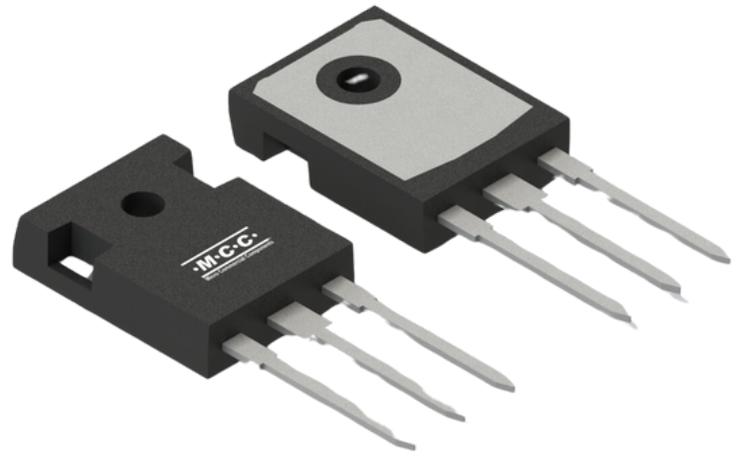


Solar Energy Systems



Leverage Faster Switching with Maximum Efficiency

MCC's New 1700V SiC MOSFET: High-Voltage Performance, Low On-Resistance



Parametrics & Datasheets:

Product	TYPE	Package	Drain-Source Voltage (VDS)	Drain- Source On-Resistance RDS(ON)	Continuous Drain Current (ID)	Datasheet
SICW400N170A-BP	SiC MOSFET	TO-247AB	1700V	400mΩ	6A	Info

Applications:



Industrial

- High-voltage power converters
- EV charging stations
- Welding equipment



Computing

- Uninterruptible power supplies (UPS)
- High-efficiency power supply units for PCs and servers
- Base station power supplies
- Network power management systems



Renewable Energy

- Solar energy systems
- Energy storage systems (ESS)

CONTACT MCC TO REQUEST A SAMPLE

mccsemi.com | +818.701.4933

